N-Channel Enhancement Mode Power MOSFET

Description

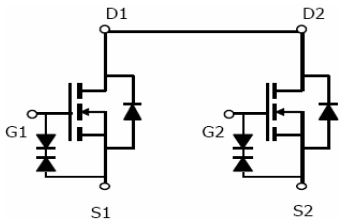
The FTK2010TSSOP uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

General Features

- V_{DS} = 20V,I_D =7A
  $R_{DS(ON)}$ < 24mΩ @ V_{GS}=2.5V
  $R_{DS(ON)}$ < 18mΩ @ V_{GS}=4.5V
  ESD Rating: 2000V HBM
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM application
- Load switch



Schematic diagram

Marking and pin assignment

TSSOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2010E	FTK2010TSSOP	TSSOP-8	Ø330mm	12mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	7	A
Drain Current-Pulsed (Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83.3	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20	21.5	23	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±10V,V_{DS}=0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.5	0.7	0.9	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=6.5A	-	13	18	mΩ
		V_{GS}=2.5V, I_D=5.5A	-	17	24	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=7A	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	1150	-	PF
Output Capacitance	C_{oss}		-	185	-	PF
Reverse Transfer Capacitance	C_{rss}		-	145	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,R_L=1.35Ω V_{GS}=5V,R_{GEN}=3Ω	-	6		nS
Turn-on Rise Time	t_r		-	13		nS
Turn-Off Delay Time	$t_{d(off)}$		-	52		nS
Turn-Off Fall Time	t_f		-	16		nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=7A, V_{GS}=4.5V	-	15		nC
Gate-Source Charge	Q_{gs}		-	0.8	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=1A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Characteristics

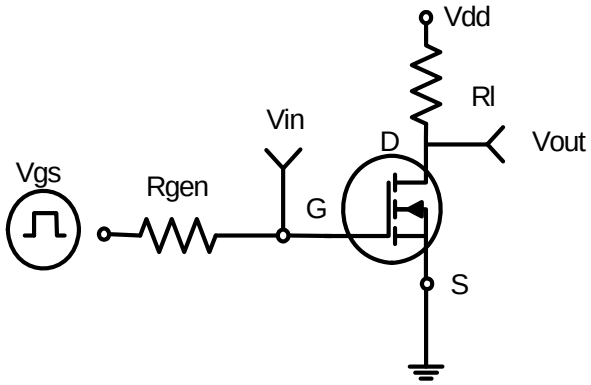


Figure 1. Switching Test Circuit

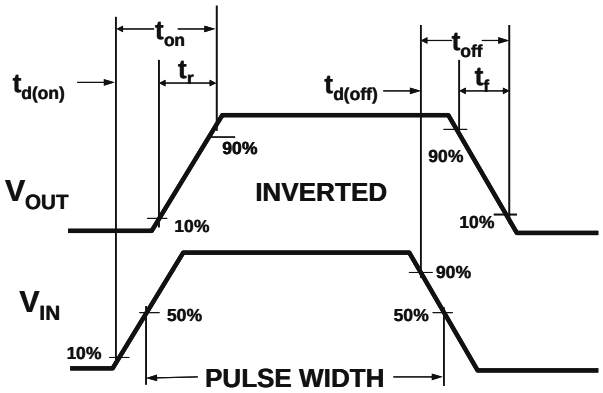


Figure 2. Switching Waveforms

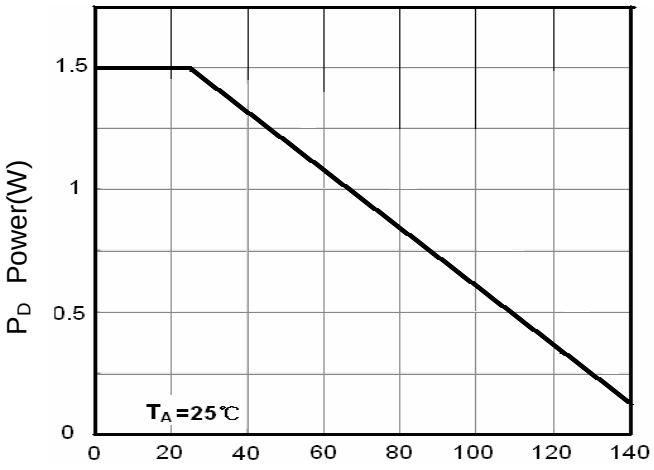


Figure 3. Power Dissipation

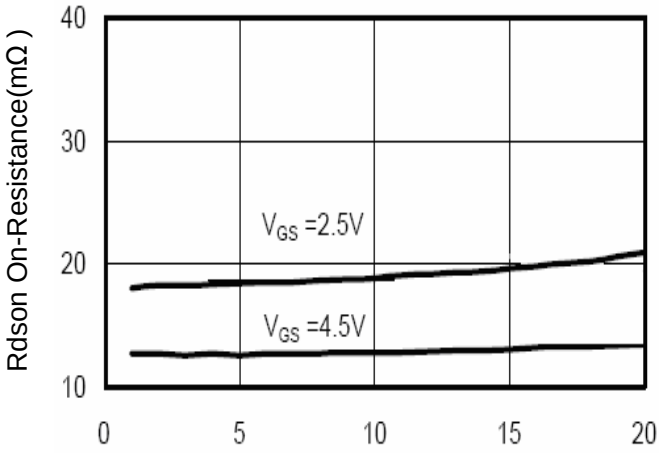


Figure 4. Drain-Source On-Resistance

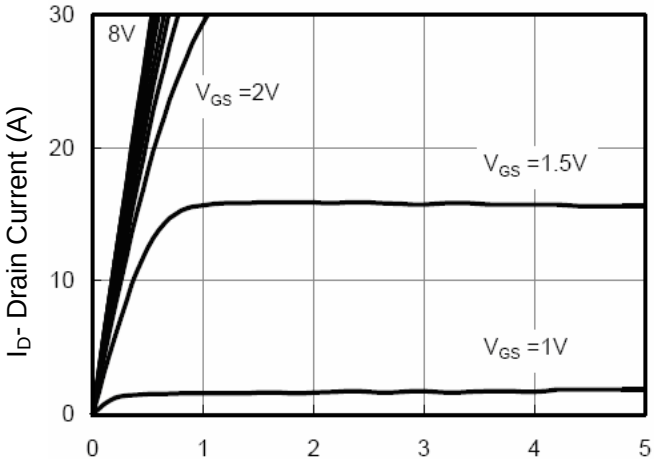


Figure 5. Output Characteristics

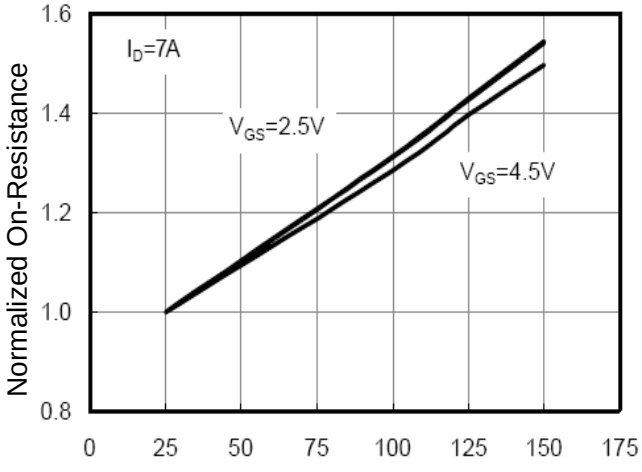


Figure 6. Drain-Source On-Resistance

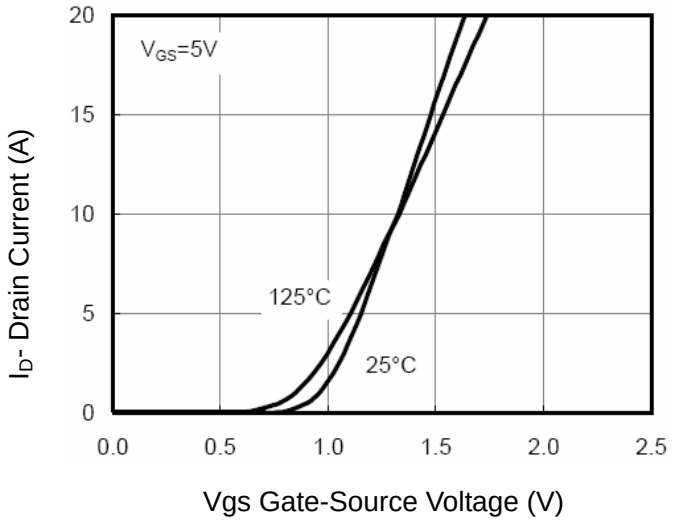


Figure 7. Transfer Characteristics

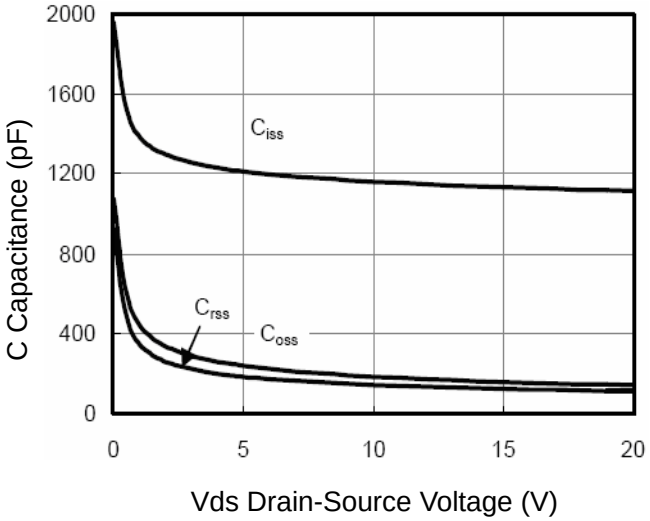


Figure 8. Capacitance vs Vds

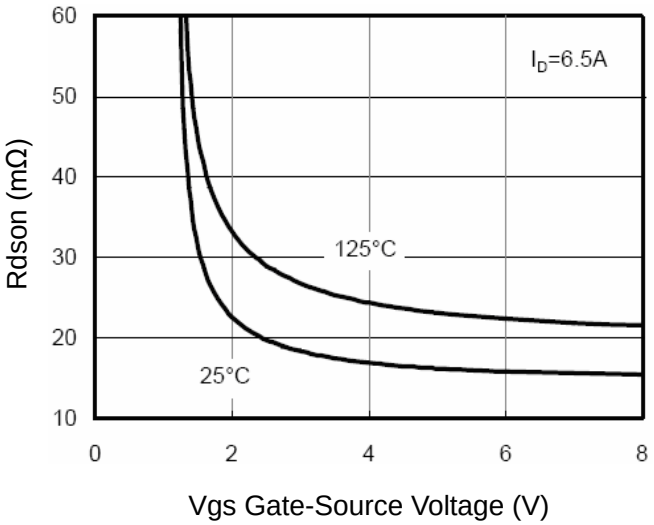


Figure 9. Rdson vs Vgs

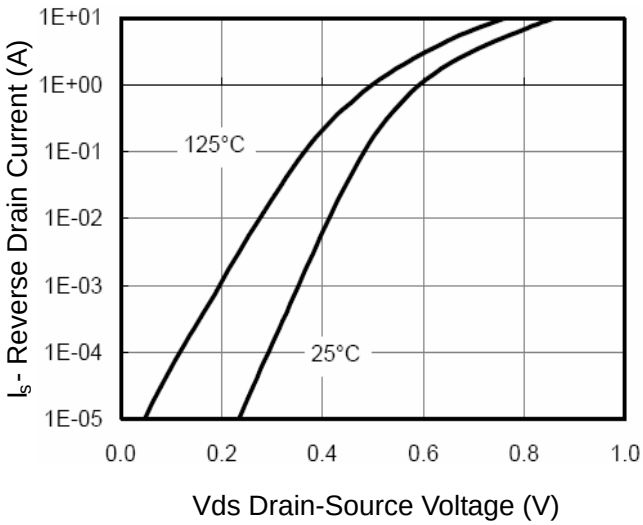


Figure 10. Capacitance vs Vds

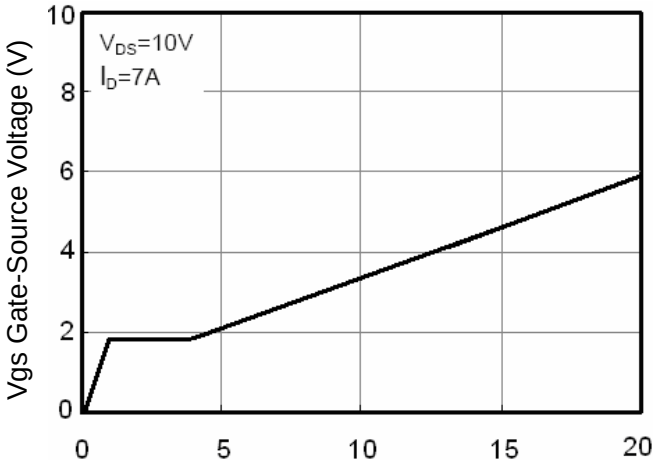


Figure 11. Gate Charge

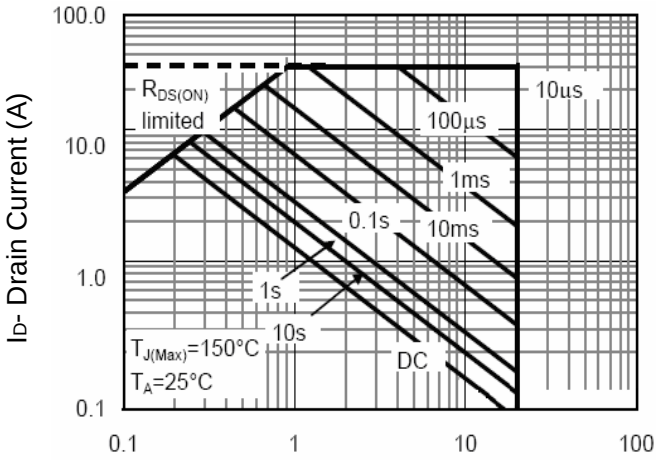


Figure 12. Safe Operation Area

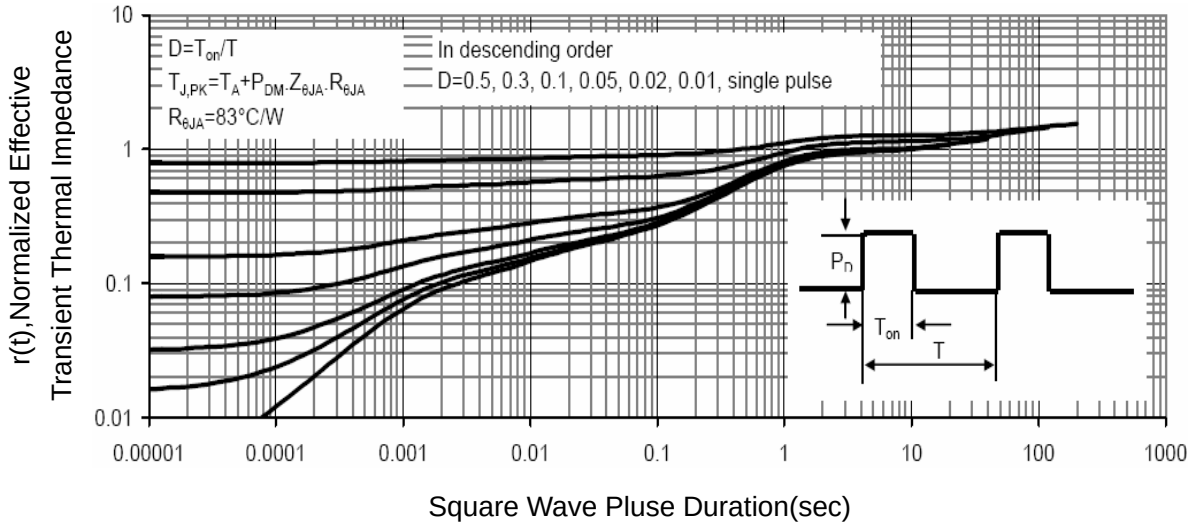
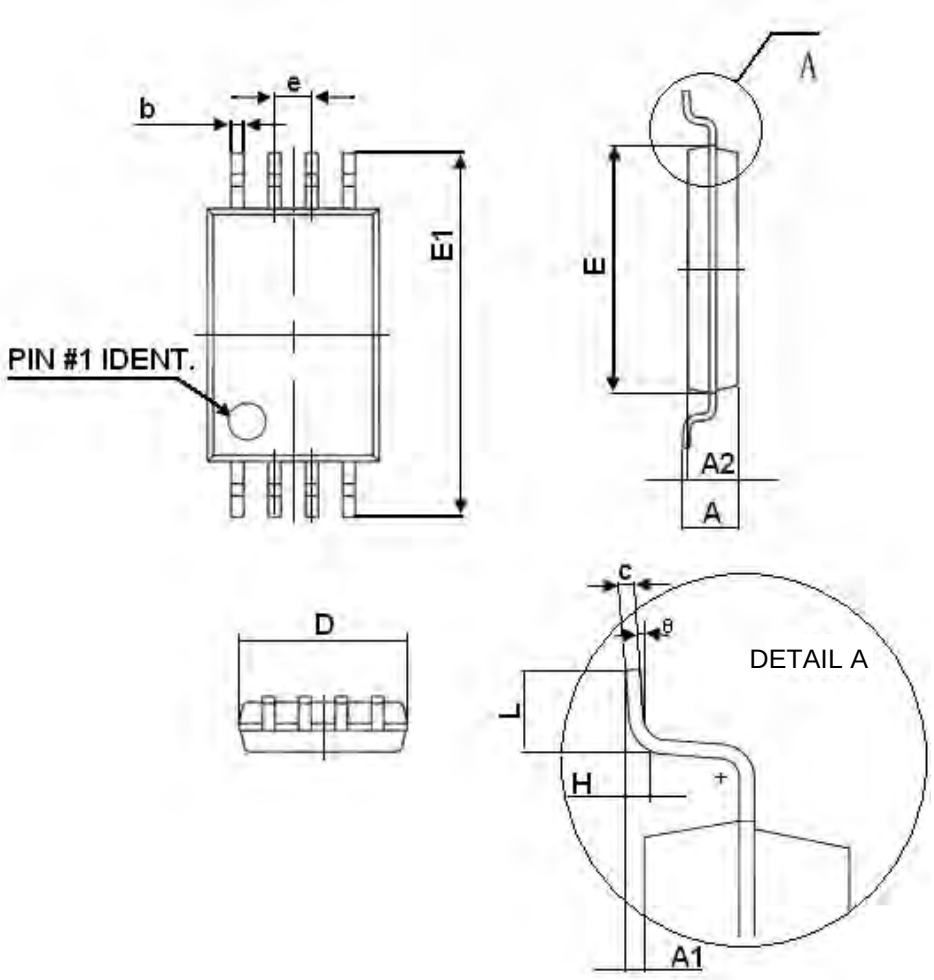


Figure 13. Normalized Maximum Transient Thermal Impedance

TSSOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
θ	1°	7°